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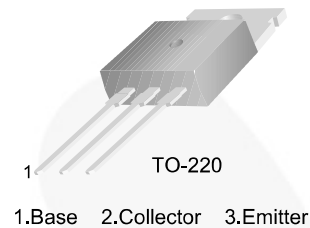
November 2014

TIP30C

PNP Epitaxial Silicon Transistor

Features

- Medium Power Linear Switching Applications
- Complementary to TIP29 Series



Ordering Information

Part Number	Top Mark	Package	Packing Method
TIP30C	TIP30C	TO-220 3L (Single Gauge)	Bulk
TIP30CTU	TIP30C	TO-220 3L (Single Gauge)	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current (DC)	-1	A
I_{CP}	Collector Current (Pulse)	-3	A
I_B	Base Current	-0.4	A
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-65 to 150	$^\circ\text{C}$

Thermal Characteristics

Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_C	Collector Dissipation ($T_A = 25^\circ\text{C}$)	2	W
	Collector Dissipation ($T_C = 25^\circ\text{C}$)	30	

Electrical Characteristics

Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage ⁽¹⁾	$I_C = -30\text{ mA}, I_B = 0$	-100		V
I_{CEO}	Collector Cut-Off Current	$V_{CE} = -60\text{ V}, I_B = 0$		-0.3	mA
I_{CES}	Collector Cut-Off Current	$V_{CE} = -100\text{ V}, V_{EB} = 0$		-200	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = -5\text{ V}, I_C = 0$		-1.0	mA
h_{FE}	DC Current Gain ⁽¹⁾	$V_{CE} = -4\text{ V}, I_C = -0.2\text{ A}$	40		
		$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$	15	75	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ⁽¹⁾	$I_C = -1\text{ A}, I_B = -125\text{ mA}$		-0.7	V
$V_{BE(on)}$	Base-Emitter On Voltage ⁽¹⁾	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$		-1.3	V
f_T	Current Gain Bandwidth Product	$V_{CE} = -10\text{ V}, I_C = -200\text{ mA}, f = 1\text{ MHz}$	3.0		MHz

Note:

1. Pulse test: $p_w \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Typical Performance Characteristics

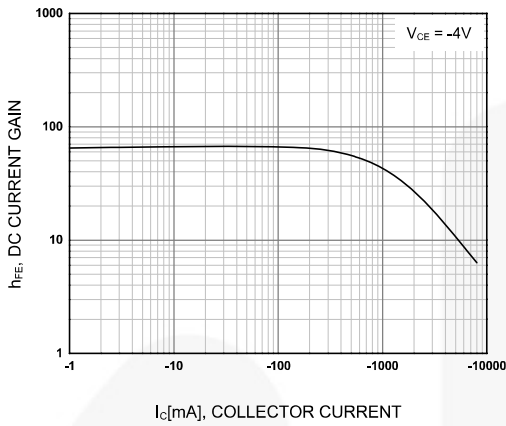


Figure 1. DC Current Gain

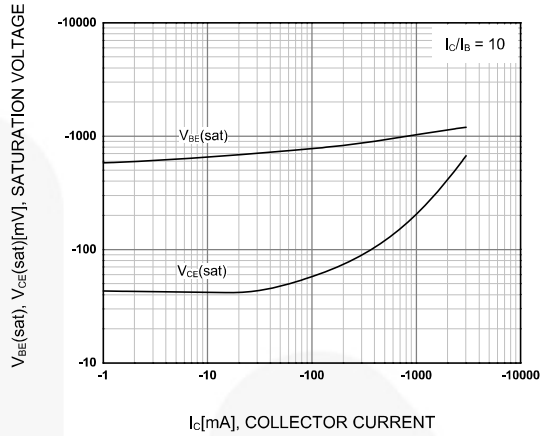


Figure 2. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

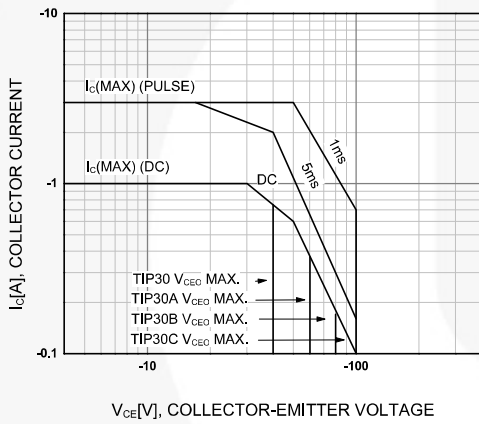


Figure 3. Safe Operating Area

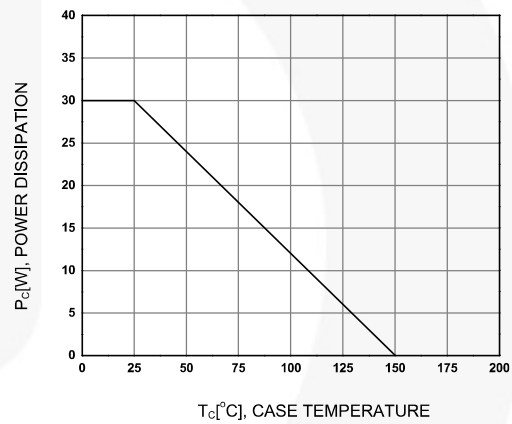


Figure 4. Power Derating

Physical Dimensions

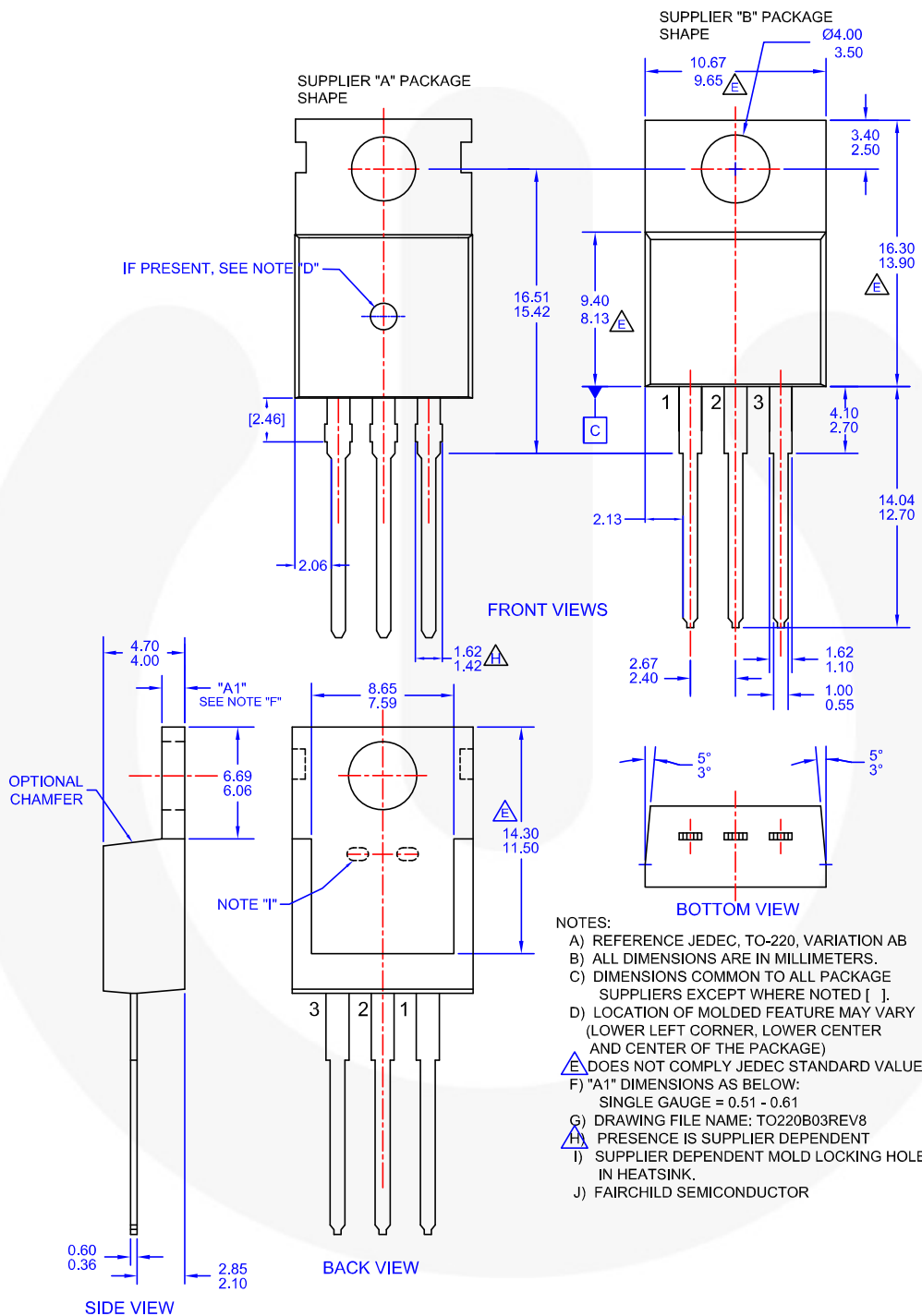


Figure 5. TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB